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Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33	- -	MAX.	50	mA
				70	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3k	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	80	mA
				120	
I_H	I_T=500mA		MAX.	80	mA
dV/dt	V_D=540V Gate Open T_j=125		MIN.	1000	V s
(dV/dt)c	(dI/dt)c=13.3A/ms, T_j=125		MIN.	12	9 V
t_{on}	I_G=80mA I_A=250mA I_R=25mA T_j=25		TYP.	3	s
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=35A t_p=380 s	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.75	V
R_D	Dynamic resistance	T_j=125	18	P
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=125	2	mA



PACKAGE MECHANICAL DATA



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